

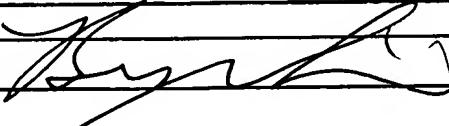
Substitute for Form 1449 A & B/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application Number	10/540,514
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>3</sup> (if known)		
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
TL	JP	06-163599	A		06-10-1994	NEC Corp.	Abstract
R1	JP	06-84959	A		03-25-1994	Fujitsu Ltd.	Abstract
RL	JP	2001-210819	A		08-03-2001	Hitachi Cable Ltd.	Abstract
TL	JP	06-21106	A		01-28-1994	Hitachi Cable Ltd.	Abstract
TL	JP	2708863	B2		10-17-1997	Sanyo Electric Co., Ltd.	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
RL		Feng Zhao et al., "Hall and photoluminescence studies of effects of the thickness of an additional In <sub>0.3</sub> Ga <sub>0.85</sub> As/Al <sub>0.25</sub> Ga <sub>0.75</sub> As/GaAs high electron mobility transistors", <i>Materials Science in Semiconductor Processing</i> , Vol. 5, 2000, pp. 23-26	
RL		U. Strauss et al., "Carrier mobilities in graded In <sub>x</sub> Ga <sub>1-x</sub> As/Al <sub>0.2</sub> Ga <sub>0.8</sub> As quantum wells for high electron mobility transistors", <i>J. Appl. Phys.</i> , Vol. 80, No. 1, July 1, 1996, pp. 322-325	
RL		J.W. Matthews et al., "Defects in Epitaxial Multilayers", <i>Journal of Crystal Growth</i> , Vol. 27, 1974, pp. 118-125	
RL		J.W. Matthews et al., "Defects in Epitaxial Multilayers", <i>Journal of Crystal Growth</i> , Vol. 32, 1976, pp. 265-273	

Examiner Signature		Date Considered	2/14/2006
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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